Silicon N-Channel MOS FET

HITACHI

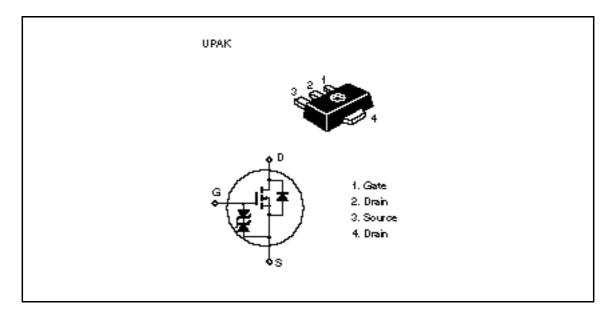
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary Breakdown
- Suitable for switching regulator and DC-DC converter

Outline





Absolute Maximum Ratings (Ta = 25° C)

Item	Symbol	Ratings	Unit	
Drain to source voltage	V _{DSS}	200	V	
Gate to source voltage	V _{GSS}	±20	V	
Drain current	I _D	1	А	
Drain peak current	I*1 D(pulse)	2	А	
Body to drain diode reverse drain current	I _{DR}	1	А	
Channel dissipation	Pch*2	1	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. PW 10 µs, duty cycle 1%

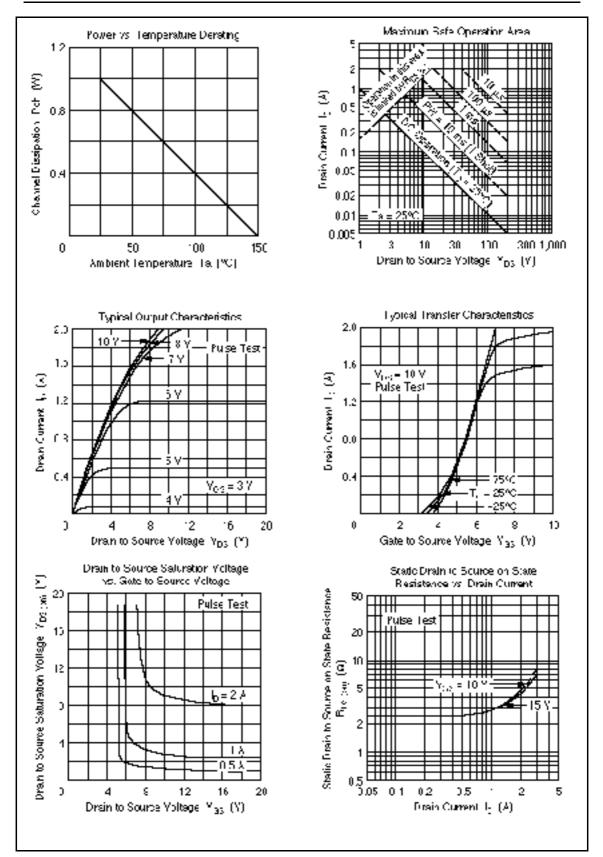
2. When using the alumina ceramic board (12.5 \times 20 \times 0.7 mm)

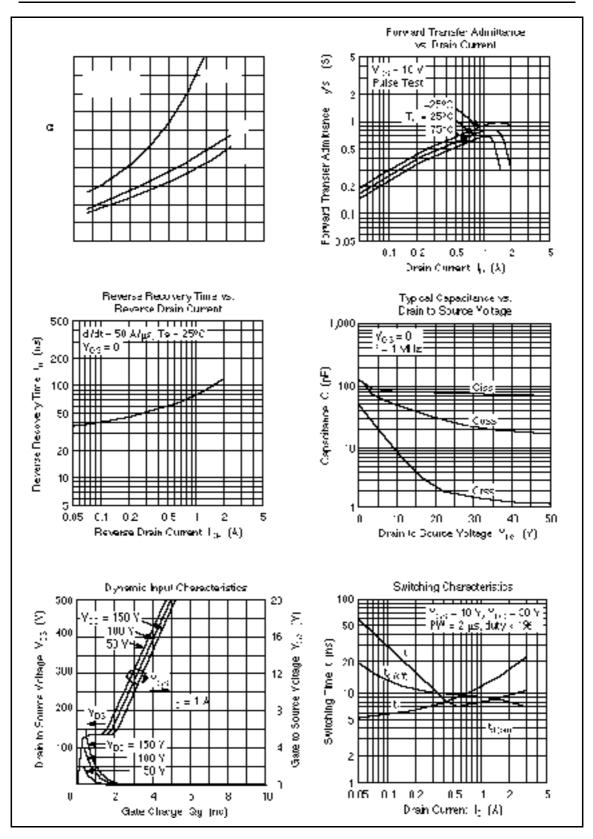
Electrical Characteristics (Ta = 25°C)

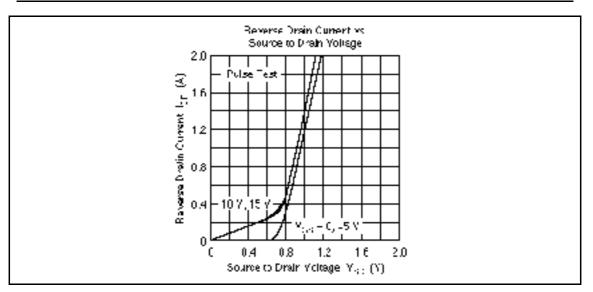
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	200	_	_	V	$I_{\rm D} = 10 \text{ mA}, V_{\rm GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	—		±10	μA	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	—		50	μA	$V_{DS} = 160 \text{ V}, \text{ V}_{GS} = 0$
Gate to source cutoff voltage	$V_{\text{GS(off)}}$	2.0		4.0	V	$I_{\rm D} = 1$ mA, $V_{\rm DS} = 10$ V
Static drain to source on state resistance	$R_{\text{DS(on)}}$	_	2.5	3.8		$I_{\rm D} = 0.5 \text{ A}, V_{\rm GS} = 10 \text{ V}^{*1}$
		_	4.5	7.0		$I_{\rm D}$ = 2 A, $V_{\rm GS}$ = 10 V * ¹
Forward transfer admittance	yfs	0.4	0.6		S	$I_{\rm D}$ = 0.5 A, $V_{\rm DS}$ = 10 V * ¹
Input capacitance	Ciss		80	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss		40	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	7	_	pF	
Turn-on delay time	t _{d(on)}	—	5	_	ns	$I_{_{ m D}}$ = 0.5 A, $V_{_{ m GS}}$ = 10 V,
Rise time	t,		8	_	ns	$R_{L} = 60$
Turn-off delay time	$t_{d(off)}$	—	10	_	ns	
Fall time	t _f	_	7	_	ns	
Body to drain diode forward voltage	V_{DF}	_	1.0	_	V	$I_{F} = 1 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t _{rr}	—	75	—	ns	$I_F = 1 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A}/\mu\text{s}$

Notes: 1. Pulse test

2. Marking for 2SK1334 is "BY".







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HITACHI

Hitachi, Ltd.

Semiconductor & IC DV. Neppon Bidg, 2-5-2, Ohte-mach, Chiyoda-ku, Tokyo 100, Japan Tet Tokyo (03, 3270-2111 Fax (03, 3270-5109

For Auther in forms Ion write to : Hischi America, Utd Semiconductor & IC DV. 2000 Sierra Point Parkway Briebana, CA. 94005-4835 U S.A. Tet 415-583-8300 Fax: 415-583-4207

Hitschi Burope GmbH Bectronic Components Group Cratinertel Burope Damacher Straße 3 D-85522 Feldkirchen Minchen Tet 089-9 94 80-0 Fex: 089-9 29 30 00 Hitschi Europe Ltd. Bedtonic Components Div. Northern Burgee Hesdguerters Whitebrook Park Lower Cook hem Road Meidenhesd Berkshire SLGSYA Urited Kingdom Tet 0528-585000 Fex 0528-778322 Hitschi Asia Pta. Ltd 45 Collyer Quay \$20-00 Hitschi Towar Singspore 0404 Tet 535-2400 Fex: 535-4533

Hitschi Asia (Hong Kong) Ltd. Unit 705, North Tower, World Finance Cantre, Herbour City, Carton Road Taim She Taui, Kowloon Hong Kong Tet 27359218 Fax: 27359218